

QUAD EXCLUSIVE OR GATE

The TC74LVQ86 is a high speed CMOS EXCLUSIVE OR GATE fabricated with silicon gate and double-layer metal wiring C²MOS technology.

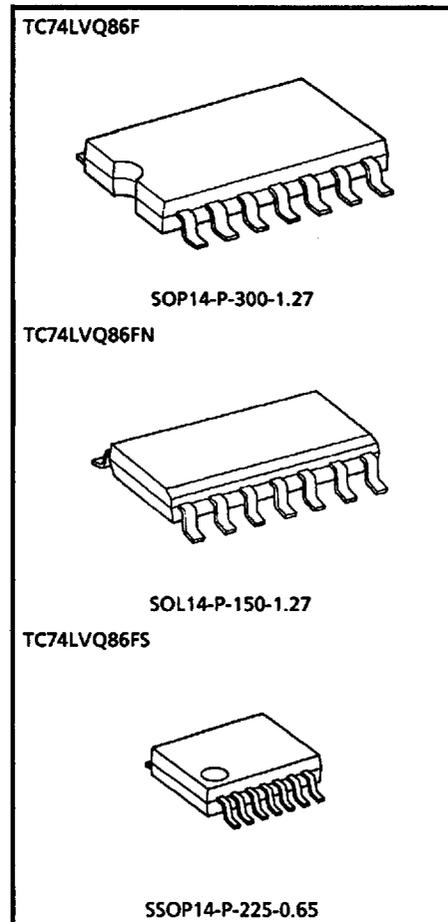
Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The internal circuit includes an output buffer, which provides high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High speed : $t_{pd} = 5.6\text{ns}$ (Typ.) ($V_{CC} = 3.3\text{V}$)
- Low power dissipation : $I_{CC} = 2.5\mu\text{A}$ (Max.) ($T_a = 25^\circ\text{C}$)
- Input voltage level : $V_{IL} = 0.8\text{V}$ (Max.) ($V_{CC} = 3\text{V}$)
 $V_{IH} = 2.0\text{V}$ (Min.) ($V_{CC} = 3\text{V}$)
- Symmetrical output impedance : $|I_{OH}| = I_{OL} = 12\text{mA}$ (Min.)
- Balanced propagation delays : $t_{pLH} \approx t_{pHL}$
- Pin and function compatible with 74HC86



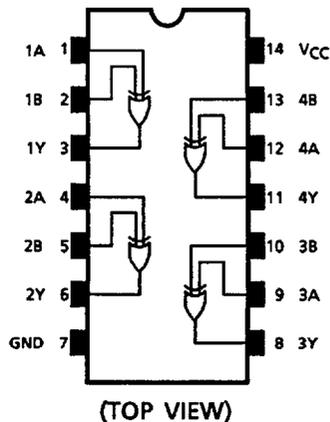
Weight
 SOP14-P-300-1.27 : 0.18g (Typ.)
 SOL14-P-150-1.27 : 0.12g (Typ.)
 SSOP14-P-225-0.65 : 0.07g (Typ.)

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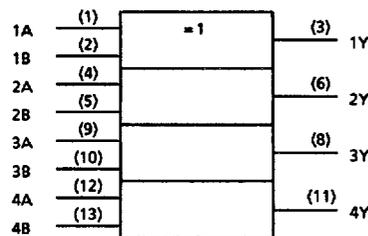
PIN ASSIGNMENT



TRUTH TABLE

INPUTS		OUTPUTS
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

IEC LOGIC SYMBOL



MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC}+0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC}+0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} / Ground Current	I_{CC}	± 100	mA
Power Dissipation	P_D	180	mW
Storage Temperature	T_{stg}	-65~150	$^{\circ}C$

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RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	2.0~3.6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise And Fall Time	dt/dv	0~100	ns/V

ELECTRICAL CHARACTERISTICS

DC characteristics

PARAMETER	SYM-BOL	TEST CONDITION	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT		
				MIN.	TYP.	MAX.	MIN.	MAX.			
Input Voltage	"H" Level	V _{IH}	3.0	2.0	—	—	2.0	—	V		
	"L" Level	V _{IL}	3.0	—	—	0.8	—	0.8			
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA	3.0	2.9	3.0	—	2.9	—	V
				I _{OH} = -12mA	3.0	2.58	—	—	2.48	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA	3.0	—	0.0	0.1	—	0.1	
				I _{OL} = 12mA	3.0	—	—	0.36	—	0.44	
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND	3.6	—	—	±0.1	—	±1.0	μA		
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	3.6	—	—	2.5	—	25.0	μA		

AC characteristics (Input t_r = t_f = 3ns, C_L = 50pF, R_L = 500Ω)

PARAMETER	SYM-BOL	TEST CONDITION	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t _{pLH}		2.7	—	7.8	16.2	1.0	18.0	ns
	t _{pHL}		3.3 ± 0.3	—	6.5	11.5	1.0	12.5	
Output To Output Skew	t _{osLH}	(Note 1)	2.7	—	—	1.5	—	1.5	ns
	t _{osHL}		3.3 ± 0.3	—	—	1.5	—	1.5	
Input Capacitance	C _{IN}	(Note 2)		—	5	10	—	10	pF
Power Dissipation Capacitance	C _{PD}	(Note 3)		—	27	—	—	—	pF

(Note 1) Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

(Note 2) Parameter guaranteed by design.

(Note 3) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per Gate)}$$

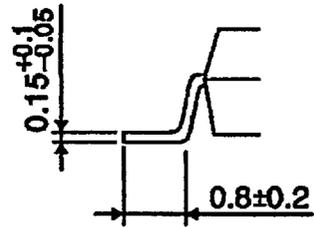
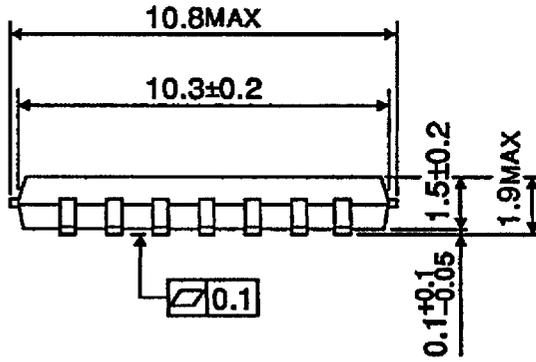
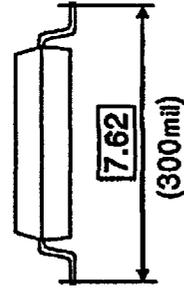
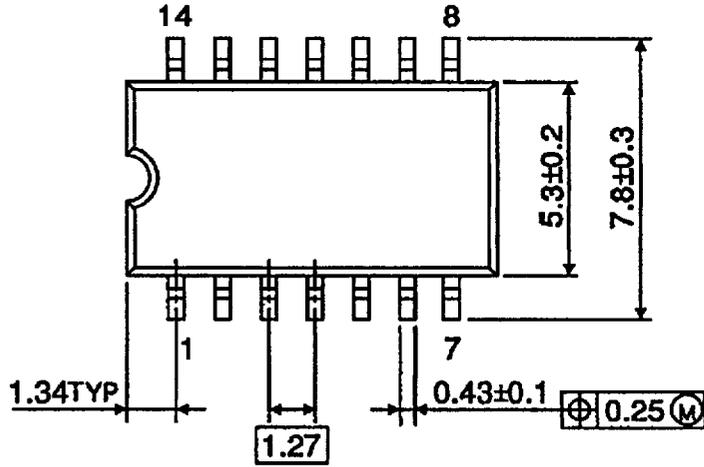
Noise characteristics (Ta = 25°C, Input tr = tf = 3ns, CL = 50pF, RL = 500Ω)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	LIMIT	UNIT
Quiet Output Maximum Dynamic VOL	VOLP		3.3	0.3	0.8	V
Quiet Output Minimum Dynamic VOL	VOLV		3.3	-0.3	-0.8	V
Minimum High Level Dynamic Input Voltage	VIHD		3.3	—	2.0	V
Maximum Low Level Dynamic Input Voltage	VILD		3.3	—	0.8	V

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OUTLINE DRAWING
SOP14-P-300-1.27

Unit : mm

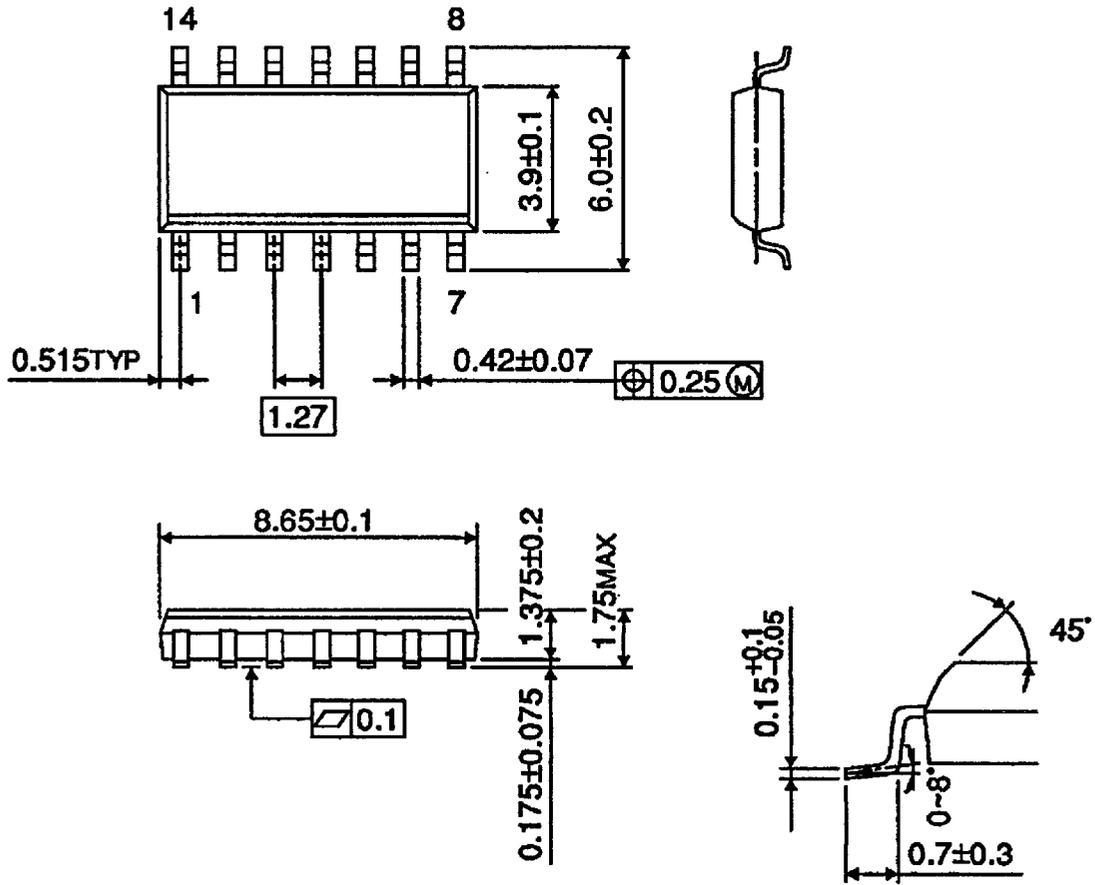


Weight : 0.18g (Typ.)

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OUTLINE DRAWING
SOL14-P-150-1.27

Unit : mm

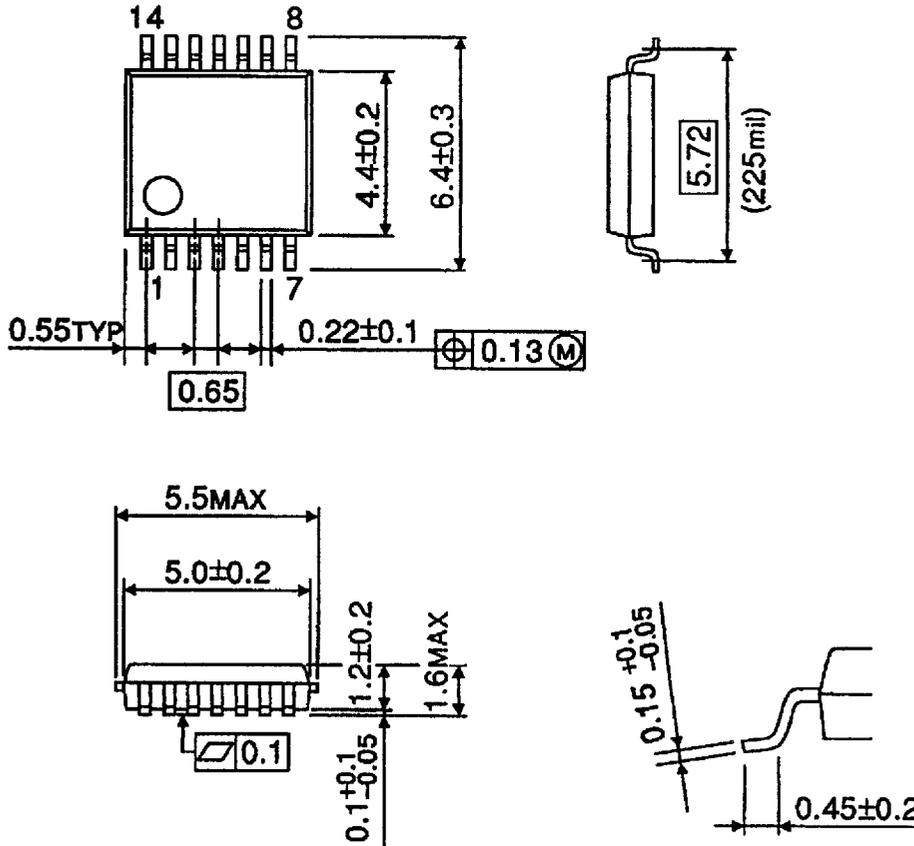


Weight : 0.12g (Typ.)

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OUTLINE DRAWING
SSOP14-P-225-0.65

Unit : mm



Weight : 0.07g (Typ.)

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